

Ready MRS (CRA)

EAST - [09917440.wsp:1]						
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	Type	Hit	Search Text	DBs	Time Stamp	
Per	43	BRS 1	"4434401" PN	USPAT	2003/06/22	
Acti	44	BRS 1	"5032786" PN	USPAT	2003/06/22	
Fail	45	BRS 1	"5179433" PN	USPAT	2003/06/22	
(46	BRS 1	"5596207" PN	USPAT	2003/06/22	
(47	BRS 1	"5548224" PN	USPAT	2003/06/22	
(48	BRS 1	"5646074" PN	USPAT	2003/06/22	
(49	BRS 1	"5739052" PN	USPAT	2003/06/22	
(50	BRS 1	"5759871" PN	USPAT	2003/06/22	
(51	BRS 1	"5781445" PN	USPAT	2003/06/22	
(52	BRS 1	"5804975" PN	USPAT	2003/06/22	
(53	BRS 1	"6028324" PN	USPAT	2003/06/22	
(54	BRS 1	"6043102" PN	USPAT	2003/06/22	
Save	55	BRS 35	"6028324" "5596207" "5179433" "6040199"	USPAT; US-PGPUB	2003/06/22	
(56	BRS 22	"6496959" "5032786" "5804975" "6043102"	USPAT; US-PGPUB	2003/06/22	
(57	BRS 1	"4542340" PN	USPAT	2003/06/22	
(58	BRS 1	"4588946" PN	USPAT	2003/06/22	
(59	BRS 1	"5420520" PN	USPAT	2003/06/22	
(60	BRS 1	"5600578" PN	USPAT	2003/06/22	
(61	BRS 1	"4382229" PN	USPAT	2003/06/22	
(62	BRS 1	"4520448" PN	USPAT	2003/06/22	
(63	BRS 1	"4542340" PN	USPAT	2003/06/22	
(64	BRS 1	"4789825" PN	USPAT	2003/06/22	
(65	BRS 1	"4906921" PN	USPAT	2003/06/22	
(66	BRS 1	"5012306" PN	USPAT	2003/06/22	
(67	BRS 1	"5093275" PN	USPAT	2003/06/22	
(68	BRS 1	"5012306" PN	USPAT	2003/06/22	
(69	BRS 1	"5153510" PN	USPAT	2003/06/22	
(70	BRS 1	"5381345" PN	USPAT	2003/06/22	
(71	BRS 1	"5638006" PN	USPAT	2003/06/22	
(72	BRS 1	"5943550" PN	USPAT	2003/06/22	
(73	BRS 1	"6043102" PN	USPAT	2003/06/22	
(74	BRS 17	"5600578"	USPAT; US-PGPUB	2003/06/22	
(75	BRS 4	"5999011"	USPAT; US-PGPUB	2003/06/22	
(76	BRS 17	"5600578"	USPAT; US-PGPUB	2003/06/22	
(77	BRS 1	"5598009" PN	USPAT	2003/06/22	
(78	BRS 1	"5625288" PN	USPAT	2003/06/22	
(79	BRS 9	"5519336"	USPAT; US-PGPUB	2003/06/22	
(80	BRS 7	"6049213"	USPAT; US-PGPUB	2003/06/22	
(81	BRS 0	(substrate with gate with (doped adi ("same conductivity" or "same impurity" or "same doping")) not (sourc	USPAT; US-PGPUB	2003/06/22	
(82	BRS 7	"4859938"	USPAT; US-PGPUB	2003/06/22	
(83	BRS 1	"3440715" PN	USPAT	2003/06/22	
(84	BRS 1	"3922707" PN	USPAT	2003/06/22	
(85	BRS 1	"3922707" PN	USPAT	2003/06/22	

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		Type Hit	Search Text	DBs	Time Stamp
Per	65	BRS 1	"3943442" PN.	USPAT	2003/06/22
Acti	66	BRS 1	"4282483" PN.	USPAT	2003/06/22
Fail	67	BRS 1	"4325025" PN.	USPAT	2003/06/22
(68	BRS 1	"4567430" PN.	USPAT	2003/06/22
(69	BRS 1	"4720670" PN.	USPAT	2003/06/22
(90	BRS 1	"4859938" PN.	USPAT	2003/06/22
(91	BRS 1	"4894605" PN.	USPAT	2003/06/22
(92	BRS 1	"4906921" PN.	USPAT	2003/06/22
(93	BRS 6	"5801538"	USPAT: US-PGPUB	2003/06/22
(94	BRS 12	((test with capacitor).ab.) and (324/\$3.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22
(95	BRS 12	((complete or full) adj (transistor or fet or mosfet or igfet or misfet or mesfet or (field adj effect))) with ("in	USPAT: US-PGPUB	2003/06/22
(96	BRS 0	((complete or full) adj (transistor or fet or mosfet or igfet or misfet or mesfet or (field adj effect)) with ("in	USPAT: US-PGPUB	2003/06/22
(97	BRS 0	((complete or full) adj (transistor or fet or mosfet or igfet or misfet or mesfet or (field adj effect)) with ("in	USPAT: US-PGPUB	2003/06/22
(98	BRS 19	((gate with "via" with (deposited or formed or sputtered or placed)) and (324/\$3.ccls.)) and ((semiconductor	USPAT: US-PGPUB	2003/06/22
(99	BRS 26	(gate with "hole" with (deposited or formed or sputtered or placed)) and (324/\$3.ccls.)	USPAT: US-PGPUB	2003/06/22
(100	BRS 3	((test with capacitor).ti.) and (324/\$3.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22
(101	BRS 4	((stacked adj capacitor)) and (324/\$3.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22
(102	BRS 9	((gate with capacitor).ab.) and (324/\$3.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22
(103	BRS 12	(gate with (contact adj hole)) and (324/\$3.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22
(104	BRS 13	(gate with hole) and (324/769.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22
(105	BRS 0	((complete or full) adj (transistor or fet or mosfet or igfet or misfet or mesfet or (field adj effect)) with ("in	USPAT: US-PGPUB	2003/06/22
(106	BRS 0	((complete or full) adj (transistor or fet or mosfet or igfet or misfet or mesfet or (field adj effect)) with ("in	USPAT: US-PGPUB	2003/06/22
(107	BRS 2	((capacitor.ti.)) and (324/769.ccls.)	USPAT: US-PGPUB	2003/06/22
(108	BRS 8	"5179433"	USPAT: US-PGPUB	2003/06/25
(109	BRS 2	"5179433"	EPO: JPO: DERWENT: IBM	2003/06/25
(110	BRS 16	(gate adj depletion adj effect) and (advanced.as.)	USPAT: US-PGPUB	2003/06/25
(111	BRS 0	(gate adj depletion adj effect) and ((257/48.ccls.))	USPAT: US-PGPUB	2003/06/25
(112	BRS 1	(gate with (depletion adj effect)) and ((257/48.ccls.))	USPAT: US-PGPUB	2003/06/25
(113	BRS 1	(gate with (depletion adj effect)) and ((test or testing).ab.)	USPAT: US-PGPUB	2003/06/25
(114	BRS 0	(((depletion adj effect) and (test or testing)).ab.)	USPAT: US-PGPUB	2003/06/25
(115	BRS 0	(gate adj depletion) and ((257/48.ccls.))	USPAT: US-PGPUB	2003/06/25
(116	BRS 0	(((gate adj depletion) and (test or testing)).ab.)	USPAT: US-PGPUB	2003/06/25
(117	BRS 1	(((gate adj depletion) and ((257/\$3.ccls.) or (438/\$3.ccls.))) and ((test or testing).ab.)	USPAT: US-PGPUB	2003/06/25
(118	BRS 0	(substrate with gate with (doped adj ("same conductivity" or "same impurity" or "same doping")) not (sourc	USPAT: US-PGPUB	2003/06/25
(119	BRS 1	"3882391" PN.	USPAT	2003/06/25
(120	BRS 4	(gate adj depletion) and (324/\$3.ccls.)	USPAT: US-PGPUB	2003/06/25
(121	BRS 9	("3882391"	USPAT: US-PGPUB	2003/06/25
(122	BRS 2	(gate adj depletion) and ((test or testing or measure or measuring or measured or tested or determine or d	USPAT: US-PGPUB	2003/06/25
(123	BRS 1	("3882391"	USPAT: US-PGPUB	2003/06/25
(124	BRS 1	"6472233"	USPAT: US-PGPUB	2003/06/25
(125	BRS 2	(((thin adj gate) with depletion) and ((test or testing or measure or measuring or measured or tested or dete	USPAT: US-PGPUB	2003/06/25
(126	BRS 1	(((thin adj gate) with inversion) and ((test or testing or measure or measuring or measured or tested or dete	USPAT: US-PGPUB	2003/06/25
(127	BRS 1	"6472233"	USPAT: US-PGPUB	2003/06/25
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Dra					
	Type	Hit	Search Text	DBs	Time Stamp
Per	144	BRS 1	"5216362".PN	USPAT	2003/06/25
Acti	145	BRS 1	"5485091".PN	USPAT	2003/06/25
Fail	146	BRS 1	"5498974".PN	USPAT	2003/06/25
(147	BRS 1	"5661408".PN	USPAT	2003/06/25
(148	BRS 1	"5773989".PN	USPAT	2003/06/25
(149	BRS 1	"5834941".PN	USPAT	2003/06/25
(150	BRS 8	(324/\$3.ccls.) and (depletion adi effect)	USPAT; US-PGPUB	2003/06/25
(151	BRS 1	(gate with accumulation with depletion) and (257/48.ccls.)	USPAT; US-PGPUB	2003/06/27
(152	BRS 5	((test or testing) adi (fet or transistor or mosfet or misfet or igfet or (field adi effect))) with "just"	USPAT; US-PGPUB	2003/06/27
(153	BRS 0	((test or testing) adi (fet or transistor or mosfet or misfet or igfet or (field adi effect))) with ((test or testing)	USPAT; US-PGPUB	2003/06/27
(154	BRS 4	((test or testing) adi (fet or transistor or mosfet or misfet or igfet or (field adi effect))) with simple	USPAT; US-PGPUB	2003/06/27
(155	BRS 1	((test or testing) adi (fet or transistor or mosfet or misfet or igfet or (field adi effect))) and ((capacitor with	USPAT; US-PGPUB	2003/06/27
(156	BRS 7	((test or testing) adi (capacitor))) and (((test or testing) adi (fet or transistor or mosfet or misfet or igfet or	USPAT; US-PGPUB	2003/06/27
(157	BRS 2	((test or testing) adi capacitor) same ((field adi oxide) or fox or locos or (local adi oxidation)))	USPAT; US-PGPUB	2003/06/27
(158	BRS 8	((test or testing) adi (gate or electrode)) same ((field adi oxide) or fox or locos or (local adi oxidation)))	USPAT; US-PGPUB	2003/06/27
(159	BRS 7	"6043662"	USPAT; US-PGPUB	2003/06/27
(160	BRS 4	((gate or electrode or poly\$1si or poly\$1silicon or (poly adi (si or silicon or crystalline)) or poly\$1crystalline)	USPAT; US-PGPUB	2003/06/27
(161	BRS 23	((gate or electrode or poly\$1si or poly\$1silicon or (poly adi (si or silicon or crystalline)) or poly\$1crystalline)	USPAT; US-PGPUB	2003/06/27
(162	BRS 20	"5798649"	USPAT; US-PGPUB	2003/06/27
(163	BRS 2	((gate or electrode or poly\$1si or poly\$1silicon or (poly adi (si or silicon or crystalline)) or poly\$1crystalline)	USPAT; US-PGPUB	2003/06/27
(164	BRS 1	"5049811".PN	USPAT	2003/06/27
(165	BRS 1	"5057441".PN	USPAT	2003/06/27
(166	BRS 1	"4296372".PN	USPAT	2003/06/27
(167	BRS 1	"5049811".PN	USPAT	2003/06/27
(168	BRS 1	"5057441".PN	USPAT	2003/06/27
(169	BRS 1	"5420513".PN	USPAT	2003/06/27
(170	BRS 3	("5798649"	USPAT; US-PGPUB	2003/06/27
(171	BRS 1	"4520448".PN	USPAT	2003/06/27
(172	BRS 1	"5049811".PN	USPAT	2003/06/27
(173	BRS 1	"5057441".PN	USPAT	2003/06/27
(174	BRS 1	"5420513".PN	USPAT	2003/06/27
(175	BRS 15	"5420513"	USPAT; US-PGPUB	2003/06/27
(176	BRS 1	gate with substrate with driven with accumulation	USPAT; US-PGPUB	2003/06/27
(177	BRS 1	"4670669".PN	USPAT	2003/06/27
(178	BRS 1	"5576565".PN	USPAT	2003/06/27
(179	BRS 1	"5608258".PN	USPAT	2003/06/27
(180	BRS 1	"5793074".PN	USPAT	2003/06/27
(181	BRS 15	capacitor with driven with accumulation	USPAT; US-PGPUB	2003/06/27
(182	BRS 34	(capacitor with accumulation) and (324/\$3.cor.)	USPAT; US-PGPUB	2003/06/27
(183	BRS 0	(capacitor with accumulation) and (257/48.ccls.)	USPAT; US-PGPUB	2003/06/27
(184	BRS 2	(substrate with accumulation) and (257/48.ccls.)	USPAT; US-PGPUB	2003/06/27
(185	BRS 36	(capacitor with depletion) and (324/\$3.ccls.)	USPAT; US-PGPUB	2003/06/27
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